

0.75-Ω SPDT ANALOG SWITCH WITH INPUT LOGIC TRANSLATION

 Check for Samples: [TS5A6542](#)

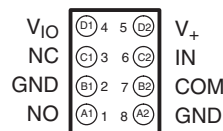
FEATURES

- Specified Break-Before-Make Switching
- Low ON-State Resistance (0.75 Ω Max)
- Control Inputs Referenced to V_{IO}
- Low Charge Injection
- Excellent ON-State Resistance Matching
- Low Total Harmonic Distortion (THD)
- 2.25-V to 5.5-V Power Supply (V_+)
- 1.65-V to 1.95-V Logic Supply (V_{IO})
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 4000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)
 - 400-V Machine Model (A115-A)

- COM Port to GND
 - 8000-V Human-Body Model (A114-B, Class II)
 - ±15-kV Contact Discharge (IEC 61000-4-2)

APPLICATIONS

- Cell Phones
- PDAs
- Portable Instrumentation

**YZP PACKAGE
(BOTTOM VIEW)**


DESCRIPTION/ORDERING INFORMATION

The TS5A6542 is a single-pole double-throw (SPDT) analog switch that is designed to operate from 2.25 V to 5.5 V. The device offers a low ON-state resistance with an excellent channel-to-channel ON-state resistance matching, and the break-before-make feature to prevent signal distortion during the transferring of a signal from one path to another. The device has excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.

The TS5A6542 has a separate logic supply pin (V_{IO}) that is characterized to operate from 1.65 V to 1.95 V. V_{IO} powers the control circuitry, which allows the TS5A6542 to be controlled by 1.8-V signals.

Table 1. ORDERING INFORMATION⁽¹⁾

T_A	PACKAGE ⁽²⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽³⁾
–40°C to 85°C	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Tape and reel	TS5A6542YZPR	___ JH7

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

(3) YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the wafer fab/assembly site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

SUMMARY OF CHARACTERISTICS⁽¹⁾

Configuration	2:1 Multiplexer/Demultiplexer (1 × SPDT)
Number of channels	1
ON-state resistance (r_{on})	0.75 Ω max
ON-state resistance match (Δr_{on})	0.1 Ω max
ON-state resistance flatness ($r_{on(flat)}$)	0.1 Ω max
Turn-on/turn-off time (t_{ON}/t_{OFF})	25 ns/20 ns
Charge injection (Q_C)	15 pC
Bandwidth (BW)	43 MHz
OFF isolation (O_{ISO})	-63 dB at 1 MHz
Crosstalk (X_{TALK})	-63 dB at 1 MHz
Total harmonic distortion (THD)	0.004%
Leakage current ($I_{NO(OFF)}/I_{NC(OFF)}$)	20 nA
Package option	8-pin WCSP

(1) $V_+ = 5\text{ V}$, $T_A = 25^\circ\text{C}$ **FUNCTION TABLE**

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
H	OFF	ON

ABSOLUTE MAXIMUM RATINGS^{(1) (2)}

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_+ V_{IO}	Supply voltage range ⁽³⁾	-0.5	6.5	V
V_{NC} V_{NO} V_{COM}	Analog voltage range ^{(3) (4) (5)}	-0.5	$V_+ + 0.5$	V
$I_{I/OK}$	Analog port diode current ⁽⁶⁾	$V_{NO}, V_{COM} < 0$ or $V_{NO}, V_{COM} > V_+$		mA
I_{NC} I_{NO} I_{COM}	On-state switch current	-450	450	mA
	On-state peak switch current ⁽⁷⁾	-700	700	
V_I	Digital input voltage range ^{(3) (4)}	-0.5	6.5	V
I_{IK}	Digital input clamp current	$V_I < 0$		mA
I_+ I_{GND}	Continuous current through V_+ or GND	-100	100	mA
T_{stg}	Storage temperature range	-65	150	°C

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.
- (6) Requires clamp diodes on analog port to V_+ .
- (7) Pulse at 1-ms duration < 10% duty cycle

THERMAL IMPEDANCE RATINGS

		UNIT
θ_{JA}	Package thermal impedance ⁽¹⁾	YZP package 102 °C/W

- (1) The package thermal impedance is calculated in accordance with JESD 51-7.

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY⁽¹⁾
 $V_+ = 4.5\text{ V to }5.5\text{ V}$, $V_{IO} = 1.65\text{ V to }1.95\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T_A	V_+	MIN	TYP	MAX	UNIT	
Analog Switch									
Analog signal range	V_{COM}, V_{NO}				0		V_+	V	
ON-state resistance	r_{on}	V_{NO} or $V_{NC} = 2.5\text{ V}$, $I_{COM} = -100\text{ mA}$, Switch ON, See Figure 14	25°C	4.5 V		0.5	0.75	Ω	
			Full			0.8			
ON-state resistance match between channels	Δr_{on}	V_{NO} or $V_{NC} = 2.5\text{ V}$, $I_{COM} = -100\text{ mA}$, Switch ON, See Figure 14	25°C	4.5 V		0.05	0.1	Ω	
			Full			0.1			
ON-state resistance flatness	$r_{on(Flat)}$	$0 \leq (V_{NO} \text{ or } V_{NC}) \leq V_+$, $I_{COM} = -100\text{ mA}$, Switch ON, See Figure 14	25°C	4.5 V		0.1		Ω	
			25°C			0.1	0.25		
			Full			0.25			
NO, NC OFF leakage current	$I_{NO(OFF)}, I_{NC(OFF)}$	$V_{NO} = 1\text{ V}, 4.5\text{ V}$, $V_{COM} = 4.5\text{ V}, 1\text{ V}$, $V_{NC} = \text{Open}$, or $V_{NC} = 1\text{ V}, 4.5\text{ V}$, $V_{COM} = 4.5\text{ V}, 1\text{ V}$, $V_{NO} = \text{Open}$, Switch OFF, See Figure 15	25°C	5.5 V		-20	2	20	nA
			Full			-100	100		
NC, NO ON leakage current	$I_{NO(ON)}$	$V_{NO} = 1\text{ V}, 4.5\text{ V}$, $V_{COM}, V_{NC} = \text{Open}$, or $V_{NC} = 1\text{ V}, 4.5\text{ V}$, $V_{COM}, V_{NO} = \text{Open}$, Switch ON, See Figure 16	25°C	5.5 V		-20	2	20	nA
			Full			-200	200		
COM ON leakage current	$I_{COM(ON)}$	$V_{COM} = 1\text{ V}, 4.5\text{ V}$, V_{NO} and $V_{NC} = \text{Open}$, or $V_{COM} = 1\text{ V}, 4.5\text{ V}$, V_{NO} or $V_{NC} = \text{Open}$, See Figure 16	25°C	5.5 V		-20	2	20	nA
			Full			-200	200		
Digital Control Input (IN)⁽²⁾									
Input logic high	V_{IH}	$V_{IO} = 1.65\text{ V to }1.95\text{ V}$	Full			$0.65 \times V_{IO}$	V_{IO}	V	
Input logic low	V_{IL}	$V_{IO} = 1.65\text{ V to }1.95\text{ V}$	Full			0	$0.35 \times V_{IO}$	V	
Input leakage current	I_{IH}, I_{IL}	$V_I = V_{IO}$ or 0	25°C	5.5 V		-2	2	nA	
			Full			-20	20		

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_{IO} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY ⁽¹⁾ (continued)
 $V_+ = 4.5\text{ V to }5.5\text{ V}$, $V_{IO} = 1.65\text{ V to }1.95\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T_A	V_+	MIN	TYP	MAX	UNIT	
Dynamic									
Turn-on time	t_{ON}	$V_{COM} = V_+$, $R_L = 50\ \Omega$,	$C_L = 35\text{ pF}$, See Figure 18	25°C	5 V	1	12.5	25	ns
				Full	4.5 V			30	
Turn-off time	t_{OFF}	$V_{COM} = V_+$, $R_L = 50\ \Omega$,	$C_L = 35\text{ pF}$, See Figure 18	25°C	5 V	1	9.5	20	ns
				Full	4.5 V			25	
Break-before-make time	t_{BBM}	$V_{NC} = V_{NO} = V_+/2$, $R_L = 50\ \Omega$,	$C_L = 35\text{ pF}$, See Figure 19	25°C	5 V	1	5	10	ns
				Full	4.5 V	1		12	
Charge injection	Q_C	$V_{GEN} = 0$, $R_{GEN} = 0$,	$C_L = 1\text{ nF}$, See Figure 23	25°C	5 V		15	pC	
NO OFF capacitance	$C_{NO(OFF)}$	$V_{NO} = V_+$ or GND, Switch OFF,	See Figure 17	25°C	5 V		37	pF	
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or $V_{NO} = V_+$ or GND, Switch ON,	See Figure 17	25°C	5 V		130	pF	
COM ON capacitance	$C_{COM(ON)}$	$V_{COM} = V_+$ or GND, Switch ON,	See Figure 17	25°C	5 V		130	pF	
Digital input capacitance	C_I	$V_I = V_{IO}$ or GND,	See Figure 17	25°C	5 V		6.5	pF	
Bandwidth	BW	$R_L = 50\ \Omega$, Switch ON,	See Figure 20	25°C	5 V		43	MHz	
OFF isolation	O_{ISO}	$R_L = 50\ \Omega$, $f = 1\text{ MHz}$,	See Figure 21	25°C	5 V		-63	dB	
Crosstalk	X_{TALK}	$R_L = 50\ \Omega$, $f = 1\text{ MHz}$,	See Figure 22	25°C	5 V		-63	dB	
Total harmonic distortion	THD	$R_L = 600\ \Omega$, $C_L = 50\text{ pF}$,	$f = 20\text{ Hz to }20\text{ kHz}$, See Figure 24	25°C	5 V		0.00 4	%	
Supply									
Positive supply current	I_+	$V_I = V_{IO}$ or GND	25°C	5.5 V		5.5	100	nA	
			Full				750		

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY⁽¹⁾
 $V_+ = 3\text{ V to }3.6\text{ V}$, $V_{IO} = 1.65\text{ V to }1.95\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch								
Analog signal range	V_{COM}, V_{NO}				0		V_+	V
ON-state resistance	r_{on}	V_{NO} or $V_{NC} = 2\text{ V}$, $I_{COM} = -100\text{ mA}$,	Switch ON, See Figure 14	25°C Full	3 V	0.75	0.9 1.2	Ω
ON-state resistance match between channels	Δr_{on}	V_{NO} or $V_{NC} = 2\text{ V}, 0.8\text{ V}$, $I_{COM} = -100\text{ mA}$,	Switch ON, See Figure 14	25°C Full	3 V	0.1	0.15 0.15	Ω
ON-state resistance flatness	$r_{on(flat)}$	$0 \leq (V_{NO} \text{ or } V_{NC}) \leq V_+$, $I_{COM} = -100\text{ mA}$,	Switch ON, See Figure 14	25°C Full	3 V	0.2 0.1	0.3 0.3	Ω
NO, NC OFF leakage current	$I_{NO(OFF)}, I_{NC(OFF)}$	$V_{NO} = 1\text{ V}, 3\text{ V}$, $V_{COM} = 3\text{ V}, 1\text{ V}$, $V_{NC} = \text{Open}$, or $V_{NC} = 1\text{ V}, 3\text{ V}$, $V_{COM} = 3\text{ V}, 1\text{ V}$, $V_{NO} = \text{Open}$,	Switch OFF, See Figure 15	25°C Full	3.6 V	-20 -50	2 50	nA
NC, NO ON leakage current	$I_{NO(ON)}$	$V_{NO} = 1\text{ V}, 3\text{ V}$, V_{NC} and $V_{COM} = \text{Open}$, or $V_{NC} = 1\text{ V}, 3\text{ V}$, V_{NO} and $V_{COM} = \text{Open}$,	Switch ON, See Figure 16	25°C Full	3.6 V	-10 -30	2 30	nA
COM ON leakage current	$I_{COM(ON)}$	$V_{COM} = 1\text{ V}$, V_{NO} and $V_{NC} = \text{Open}$, or $V_{COM} = 3\text{ V}$, V_{NO} and $V_{NC} = \text{Open}$,	See Figure 16	25°C Full	3.6 V	-10 -30	2 30	nA
Digital Control Input (IN)⁽²⁾								
Input logic high	V_{IH}	$V_{IO} = 1.65\text{ V to }1.95\text{ V}$		Full		$0.65 \times V_{IO}$	V_{IO}	V
Input logic low	V_{IL}	$V_{IO} = 1.65\text{ V to }1.95\text{ V}$		Full		0	$0.35 \times V_{IO}$	V
Input leakage current	I_{IH}, I_{IL}	$V_I = V_{IO}$ or 0		25°C Full	3.6 V	-2 -20	2 20	nA

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_{IO} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY ⁽¹⁾ (continued)
 $V_+ = 3\text{ V to }3.6\text{ V}$, $V_{IO} = 1.65\text{ V to }1.95\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T_A	V_+	MIN	TYP	MAX	UNIT	
Dynamic									
Turn-on time	t_{ON}	$V_{COM} = V_+$, $R_L = 50\ \Omega$,	$C_L = 35\text{ pF}$, See Figure 18	25°C	3.3 V	5	15	30	ns
				Full	3 V	3		35	
Turn-off time	t_{OFF}	$V_{COM} = V_+$, $R_L = 50\ \Omega$,	$C_L = 35\text{ pF}$, See Figure 18	25°C	3.3 V	1	9	20	ns
				Full	3 V	1		25	
Break-before-make time	t_{BBM}	$V_{NC} = V_{NO} = V_+/2$, $R_L = 50\ \Omega$,	$C_L = 35\text{ pF}$, See Figure 19	25°C	3.3 V	1	8	13	ns
				Full	3 V	1		15	
Charge injection	Q_C	$V_{GEN} = 0$, $R_{GEN} = 0$,	$C_L = 1\text{ nF}$, See Figure 23	25°C	3.3V		6.5	pC	
NO OFF capacitance	$C_{NO(OFF)}$	$V_{NO} = V_+$ or GND, Switch OFF,	See Figure 17	25°C	3.3 V		38	pF	
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or $V_{NO} = V_+$ or GND, Switch ON,	See Figure 17	25°C	3.3 V		133	pF	
COM ON capacitance	$C_{COM(ON)}$	$V_{COM} = V_+$ or GND, Switch ON,	See Figure 17	25°C	3.3 V		133	pF	
Digital input capacitance	C_I	$V_I = V_{IO}$ or GND,	See Figure 17	25°C	3.3 V		6.5	pF	
Bandwidth	BW	$R_L = 50\ \Omega$, Switch ON,	See Figure 20	25°C	3.3 V		42	MHz	
OFF isolation	O_{ISO}	$R_L = 50\ \Omega$, $f = 1\text{ MHz}$,	See Figure 21	25°C	3.3 V		-63	dB	
Crosstalk	X_{TALK}	$R_L = 50\ \Omega$, $f = 1\text{ MHz}$,	See Figure 22	25°C	3.3 V		-63	dB	
Total harmonic distortion	THD	$R_L = 600\ \Omega$, $C_L = 50\text{ pF}$,	$f = 20\text{ Hz to }20\text{ kHz}$, See Figure 24	25°C	3.3 V		0.00 4	%	
Supply									
Positive supply current	I_+	$V_I = V_{IO}$ or GND	25°C	3.6 V		10	50	nA	
			Full				300		

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY⁽¹⁾
 $V_+ = 2.25\text{ V to }2.75\text{ V}$, $V_{IO} = 1.65\text{ V to }1.95\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T_A	V_+	MIN	TYP	MAX	UNIT	
Analog Switch									
Analog signal range	V_{COM}, V_{NO}				0		V_+	V	
ON-state resistance	r_{on}	V_{NO} or $V_{NC} = 1.8\text{ V}$, $I_{COM} = -100\text{ mA}$,	Switch ON, See Figure 14	25°C	2.25 V	1	1.3	Ω	
				Full		1.6			
ON-state resistance match between channels	Δr_{on}	V_{NO} or $V_{NC} = 1.8\text{ V}$, 0.8 V , $I_{COM} = -100\text{ mA}$,	Switch ON, See Figure 14	25°C	2.25 V	0.15	0.2	Ω	
				Full		0.2			
ON-state resistance flatness	$r_{on(Flat)}$	$0 \leq (V_{NO} \text{ or } V_{NC}) \leq V_+$, $I_{COM} = -100\text{ mA}$,	Switch ON, See Figure 14	25°C	2.25 V	0.5		Ω	
				25°C		Full	0.25		
							0.6		
NO, NC OFF leakage current	$I_{NO(OFF)}, I_{NC(OFF)}$	$V_{NO} = 0.5\text{ V}, 2.2\text{ V}$, $V_{COM} = 2.2\text{ V}, 0.5\text{ V}$, $V_{NC} = \text{Open}$, or $V_{NC} = 0.5\text{ V}, 2.2\text{ V}$, $V_{COM} = 2.2\text{ V}, 0.5\text{ V}$, $V_{NO} = \text{Open}$,	Switch OFF, See Figure 15	25°C	2.75 V	-20	2	20	nA
				Full		-50	50		
NC, NO ON leakage current	$I_{NO(ON)}$	$V_{NO} = 0.5\text{ V}, 2.2\text{ V}$, V_{NC} and $V_{COM} = \text{Open}$, or $V_{NC} = 2.2\text{ V}, 0.5\text{ V}$, V_{NO} and $V_{COM} = \text{Open}$,	Switch ON, See Figure 16	25°C	2.75 V	-10	2	10	nA
				Full		-20	20		
COM ON leakage current	$I_{COM(ON)}$	$V_{COM} = 0.5\text{ V}$, V_{NO} and $V_{NC} = \text{Open}$, or $V_{COM} = 2.2\text{ V}$, V_{NO} and $V_{NC} = \text{Open}$,	Switch ON, See Figure 16	25°C	2.75 V	-10	2	10	nA
				Full		-20	20		
Digital Control Input (IN)⁽²⁾									
Input logic high	V_{IH}	$V_{IO} = 1.65\text{ V to }1.95\text{ V}$		Full		$0.65 \times V_{IO}$	V_{IO}	V	
Input logic low	V_{IL}	$V_{IO} = 1.65\text{ V to }1.95\text{ V}$		Full		0	$0.35 \times V_{IO}$	V	
Input leakage current	I_{IH}, I_{IL}	$V_I = V_{IO}$ or 0		25°C	2.75 V	-2	2	nA	
				Full		-20	20		

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_{IO} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY ⁽¹⁾ (continued)
 $V_+ = 2.25\text{ V to }2.75\text{ V}$, $V_{IO} = 1.65\text{ V to }1.95\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T_A	V_+	MIN	TYP	MAX	UNIT	
Dynamic									
Turn-on time	t_{ON}	$V_{COM} = V_+$, $R_L = 50\ \Omega$,	$C_L = 35\text{ pF}$, See Figure 18	25°C	2.5 V	5	20	35	ns
				Full	2.25 V	5		40	
Turn-off time	t_{OFF}	$V_{COM} = V_+$, $R_L = 50\ \Omega$,	$C_L = 35\text{ pF}$, See Figure 18	25°C	2.5 V	2	10	20	ns
				Full	2.25 V	2		25	
Break-before-make time	t_{BBM}	$V_{NC} = V_{NO} = V_+/2$, $R_L = 50\ \Omega$,	$C_L = 35\text{ pF}$, See Figure 19	25°C	2.5 V	1	11	20	ns
				Full	2.25 V	1		25	
Charge injection	Q_C	$V_{GEN} = 0$, $R_{GEN} = 0$,	$C_L = 1\text{ nF}$, See Figure 23	25°C	2.5 V		5	pC	
NO OFF capacitance	$C_{NO(OFF)}$	$V_{NO} = V_+$ or GND, Switch OFF,	See Figure 17	25°C	2.5 V		38	pF	
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or $V_{NO} = V_+$ or GND, Switch ON,	See Figure 17	25°C	2.5 V		135	pF	
COM ON capacitance	$C_{COM(ON)}$	$V_{COM} = V_+$ or GND, Switch ON,	See Figure 17	25°C	2.5 V		135	pF	
Digital input capacitance	C_I	$V_I = V_{IO}$ or GND,	See Figure 17	25°C	2.5 V		6.5	pF	
Bandwidth	BW	$R_L = 50\ \Omega$, Switch ON,	See Figure 20	25°C	2.5 V		40	MHz	
OFF isolation	O_{ISO}	$R_L = 50\ \Omega$, $f = 1\text{ MHz}$,	See Figure 21	25°C	2.5 V		-63	dB	
Crosstalk	X_{TALK}	$R_L = 50\ \Omega$, $f = 1\text{ MHz}$,	See Figure 22	25°C	2.5 V		-63	dB	
Total harmonic distortion	THD	$R_L = 600\ \Omega$, $C_L = 50\text{ pF}$,	$f = 20\text{ Hz to }20\text{ kHz}$, See Figure 24	25°C	2.5 V		0.00 8	%	
Supply									
Positive supply current	I_+	$V_I = V_{IO}$ or GND	25°C	2.75 V		10	25	nA	
			Full				100		

TYPICAL PERFORMANCE

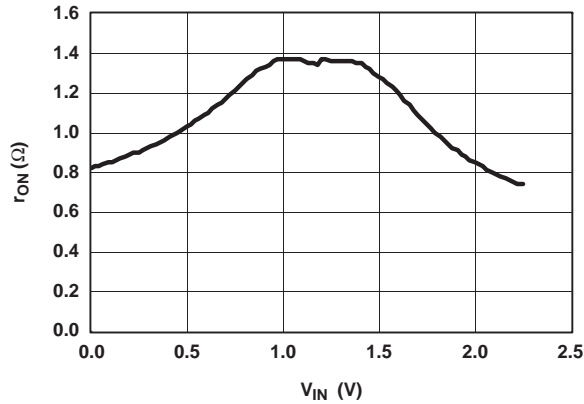


Figure 1. r_{on} vs V_{COM} ($V_+ = 2.5\text{ V}$)

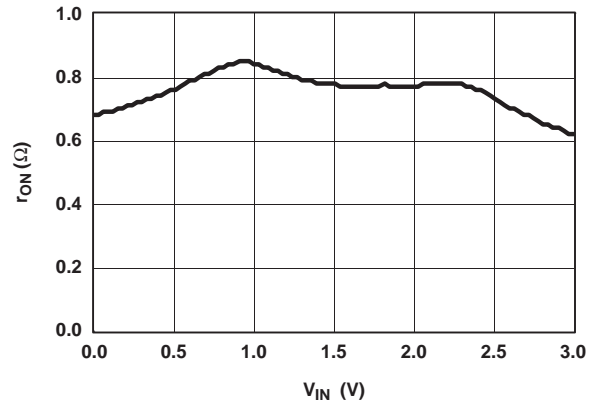


Figure 2. r_{on} vs V_{COM} ($V_+ = 3.3\text{ V}$)

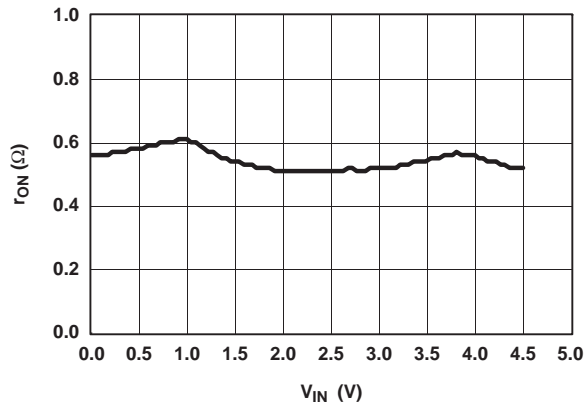


Figure 3. r_{on} vs V_{COM} ($V_+ = 5\text{ V}$)

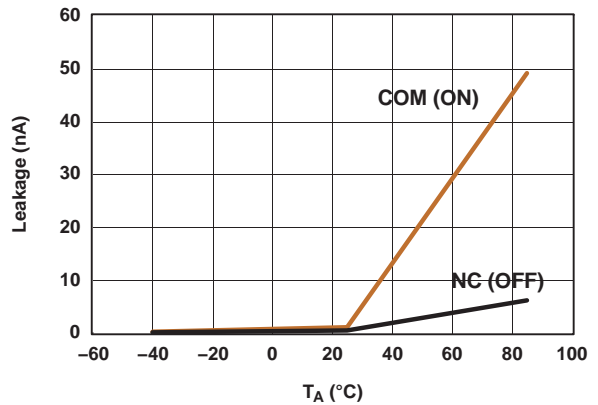


Figure 4. Leakage Current vs Temperature ($V_+ = 5\text{ V}$)

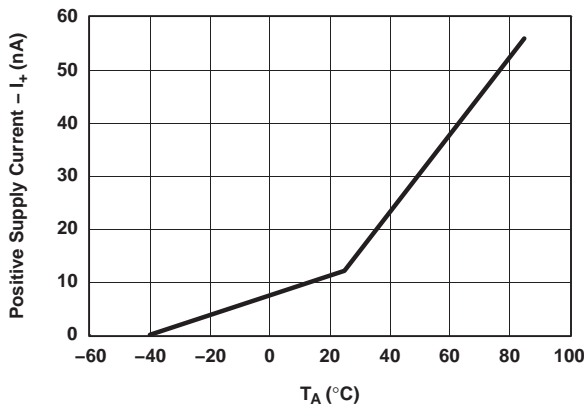


Figure 5. I_+ vs Temperature ($V_+ = 5\text{ V}$)

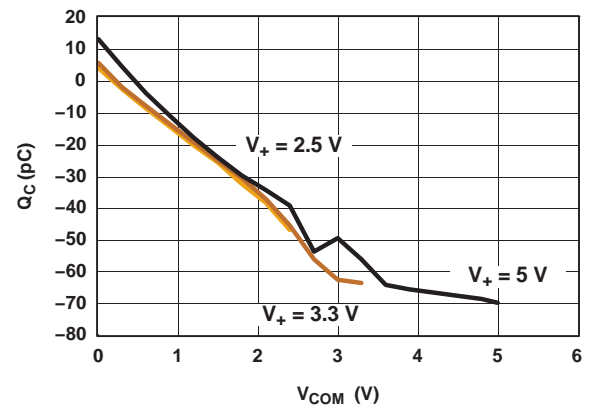


Figure 6. Charge Injection (Q_C) vs V_{COM}

TYPICAL PERFORMANCE (continued)

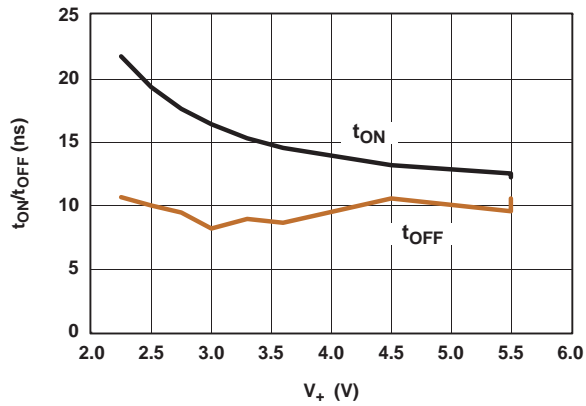


Figure 7. t_{ON}/t_{OFF} vs Supply Voltage

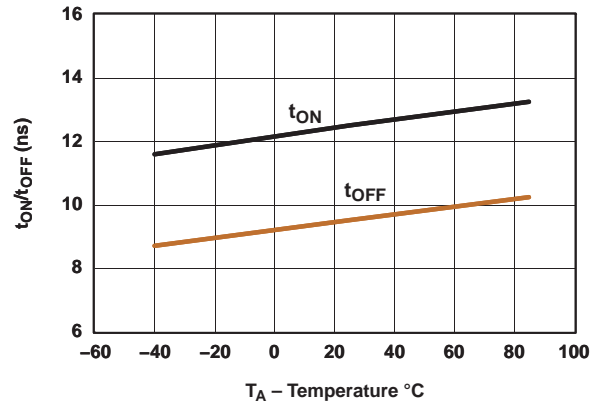


Figure 8. t_{ON}/t_{OFF} vs Temperature (V₊ = 5 V)

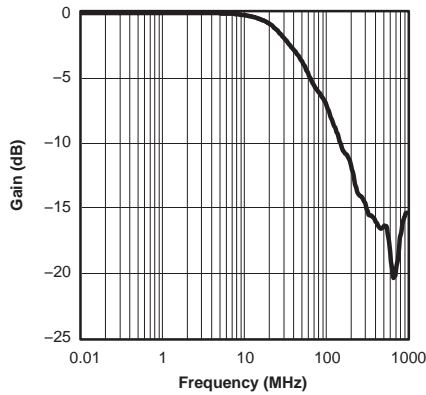


Figure 9. Gain vs Frequency (V₊ = 5 V)

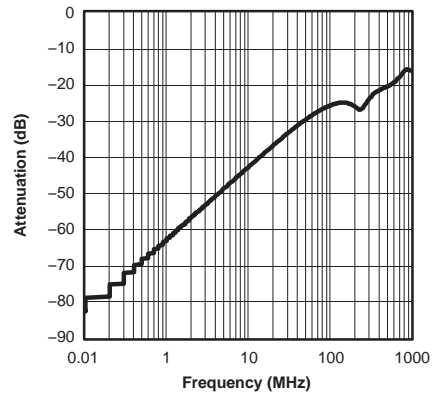


Figure 10. Crosstalk vs Frequency (V₊ = 5 V)

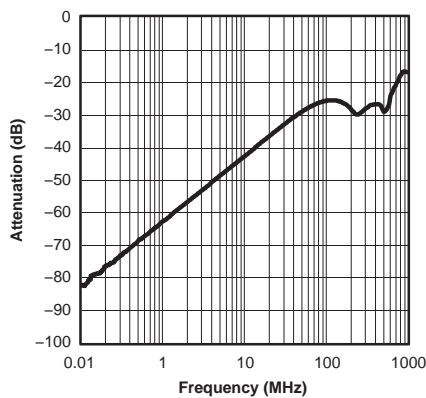


Figure 11. OFF Isolation vs Frequency (V₊ = 5 V)

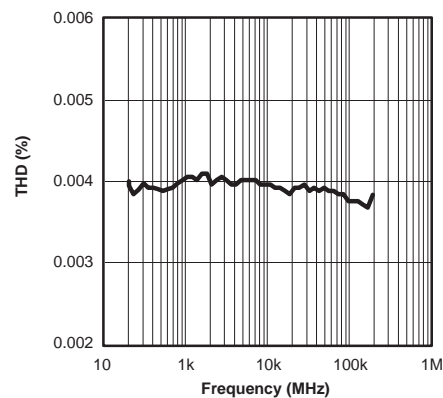


Figure 12. Total Harmonic Distortion vs Frequency (V₊ = 2.5 V)

TYPICAL PERFORMANCE (continued)

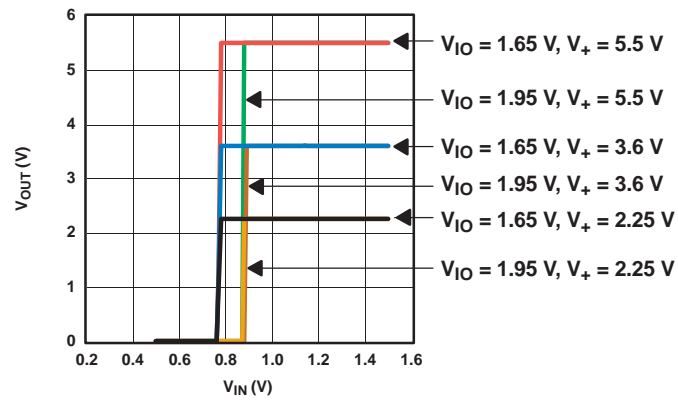


Figure 13. V_{IO} Thresholds

PARAMETER MEASUREMENT INFORMATION

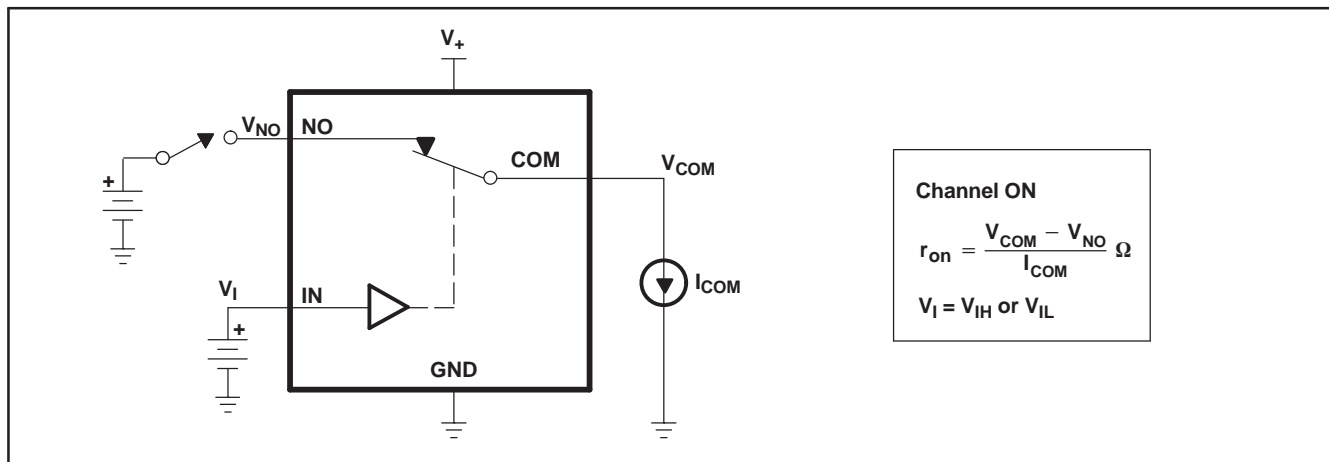


Figure 14. ON-State Resistance (r_{on})

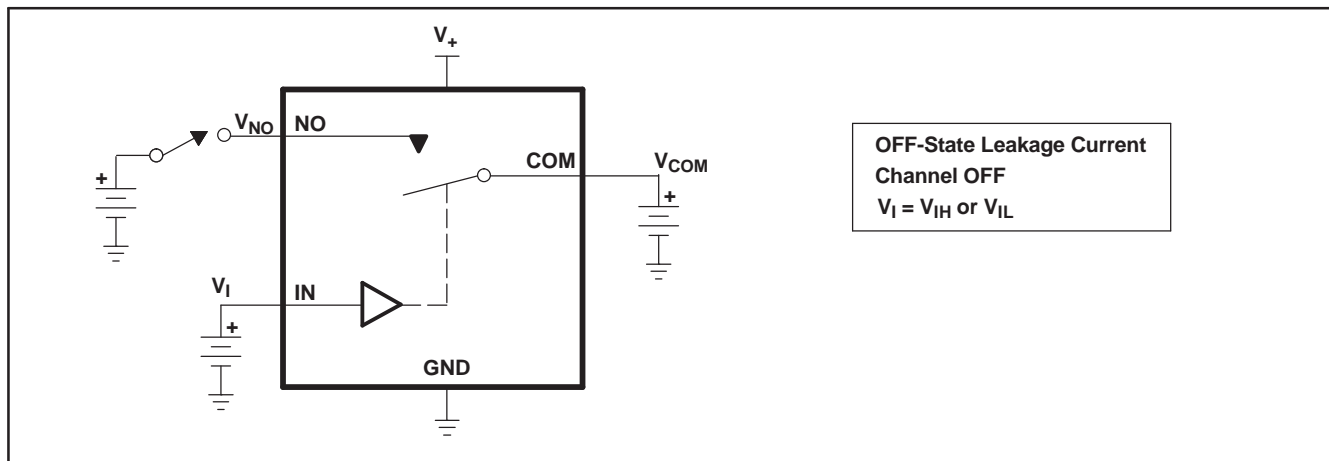


Figure 15. OFF-State Leakage Current ($I_{COM(OFF)}$, $I_{NC(OFF)}$, $I_{COM(PWROFF)}$, $I_{NC(PWRFF)}$)

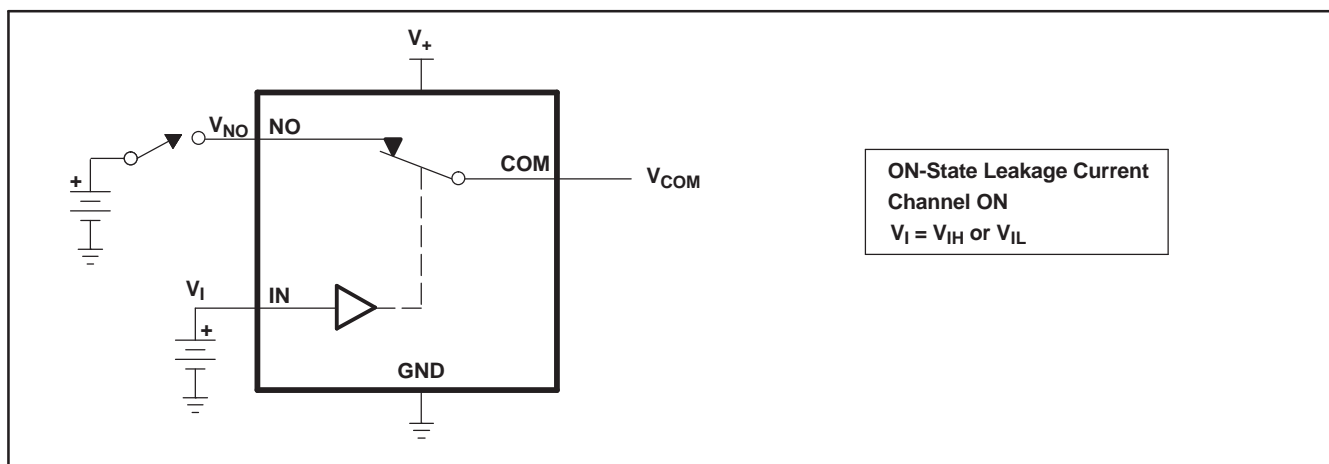


Figure 16. ON-State Leakage Current ($I_{COM(ON)}$, $I_{NC(ON)}$)

PARAMETER MEASUREMENT INFORMATION (continued)

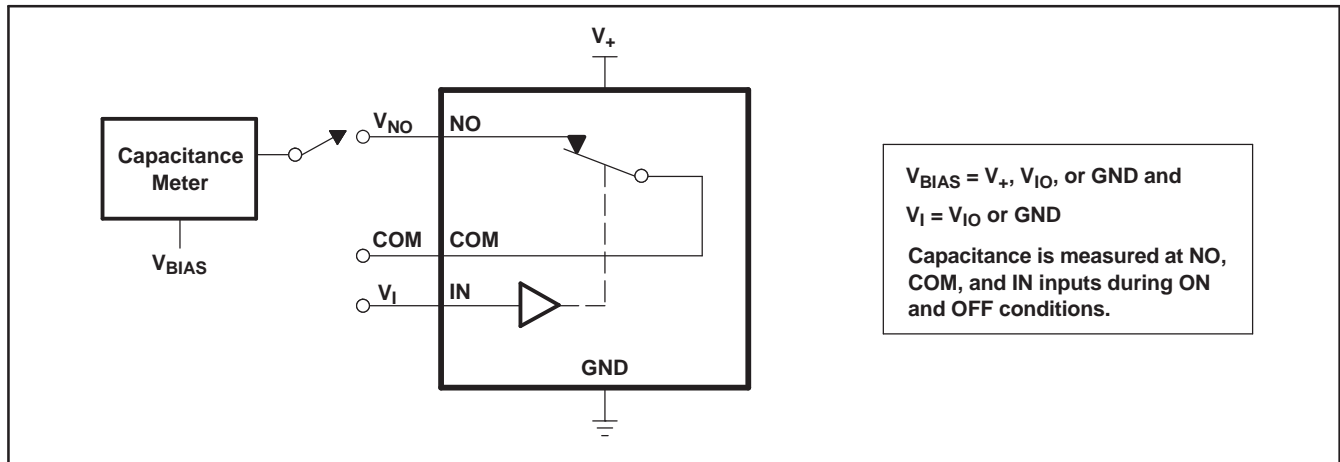
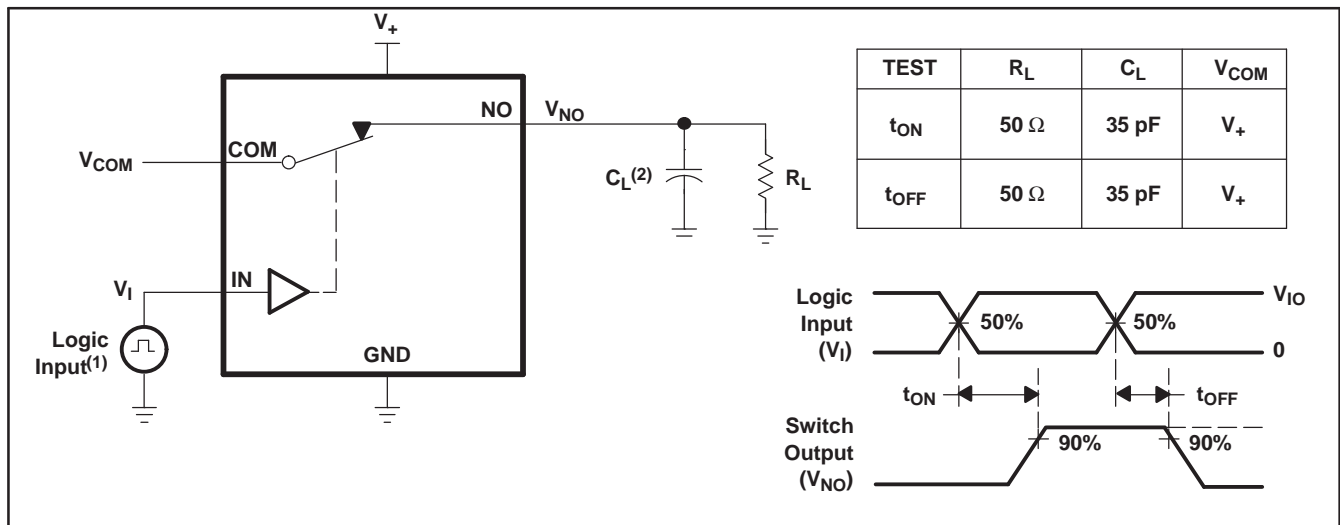


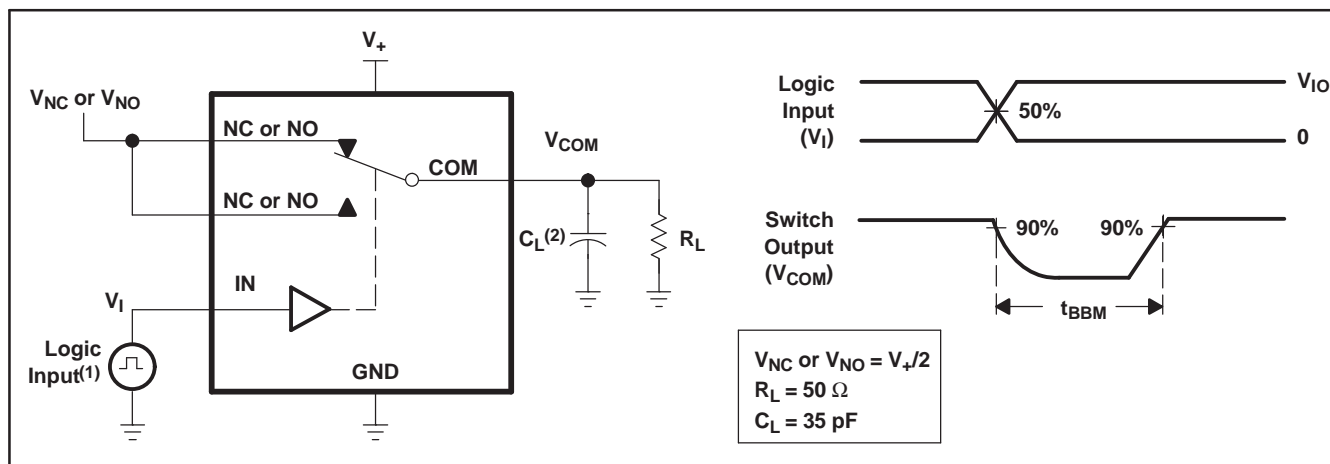
Figure 17. Capacitance (C_I , $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NC(OFF)}$, $C_{NC(ON)}$)



(1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.
 (2) C_L includes probe and jig capacitance.

Figure 18. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})

PARAMETER MEASUREMENT INFORMATION (continued)



- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.
- (2) C_L includes probe and jig capacitance.

Figure 19. Break-Before-Make Time (t_{BBM})

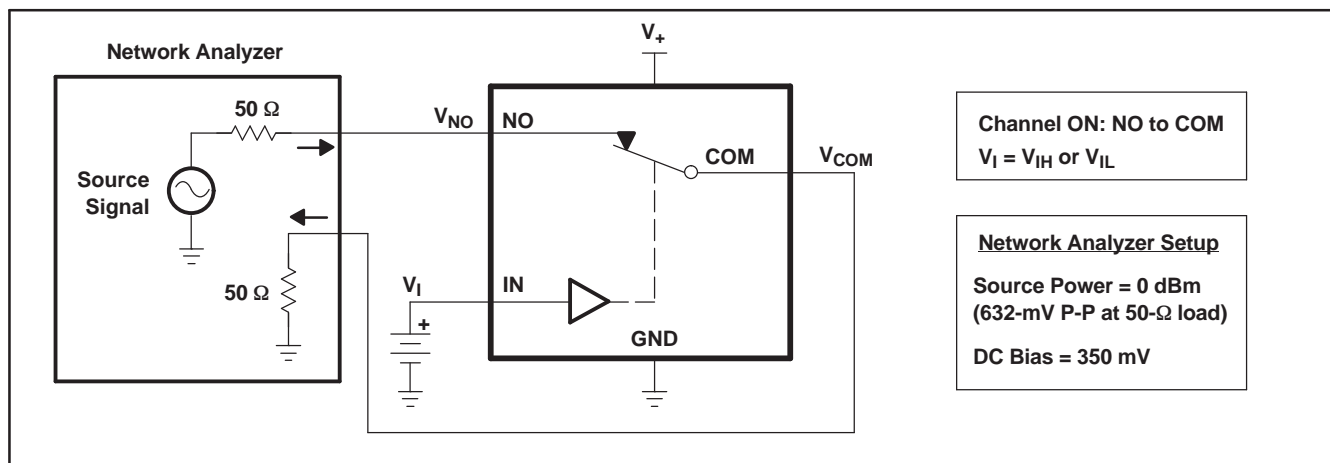


Figure 20. Bandwidth (BW)

PARAMETER MEASUREMENT INFORMATION (continued)

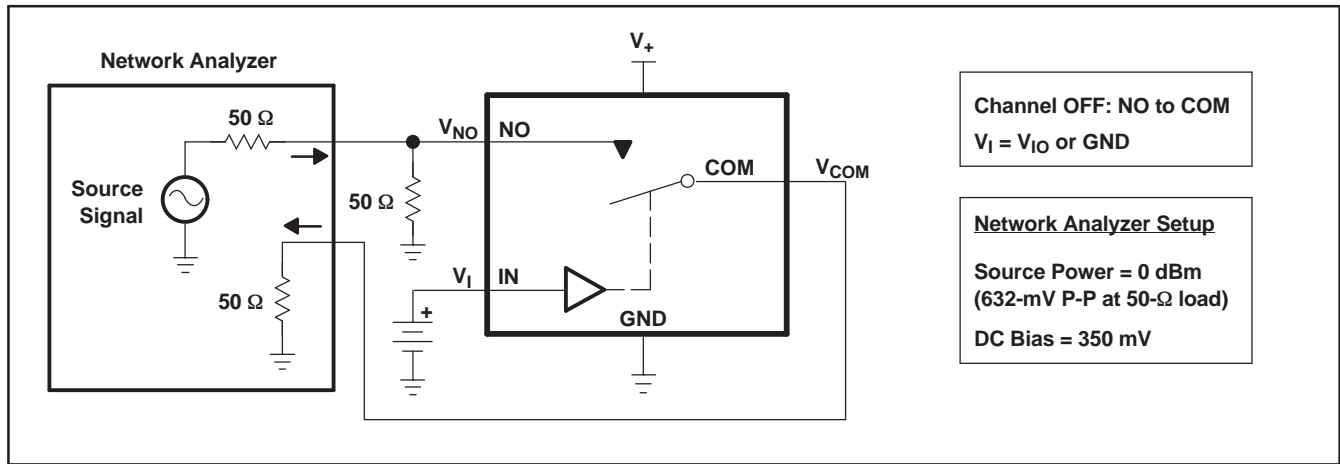


Figure 21. OFF Isolation (O_{ISO})

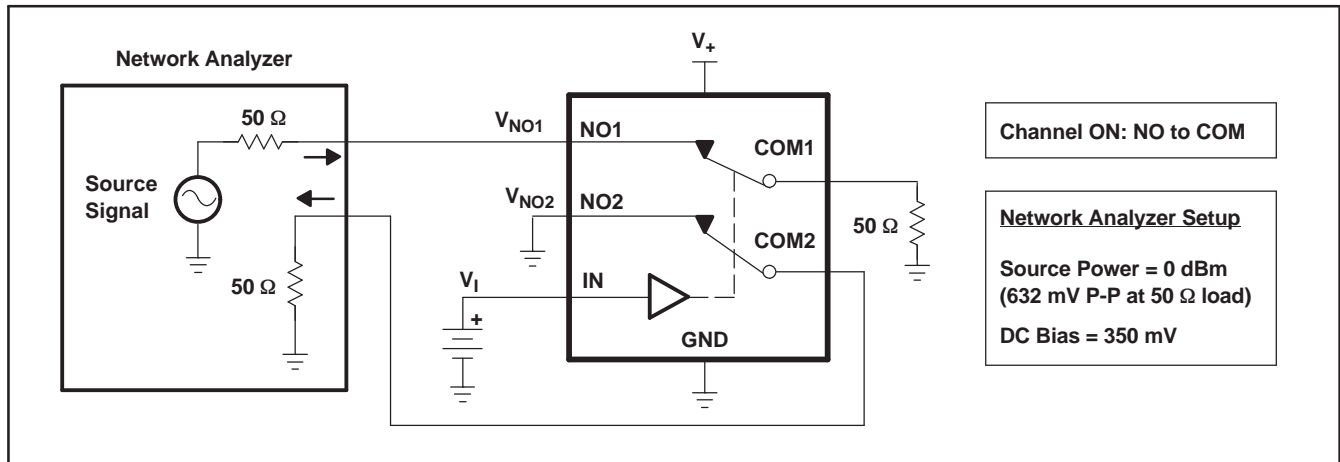
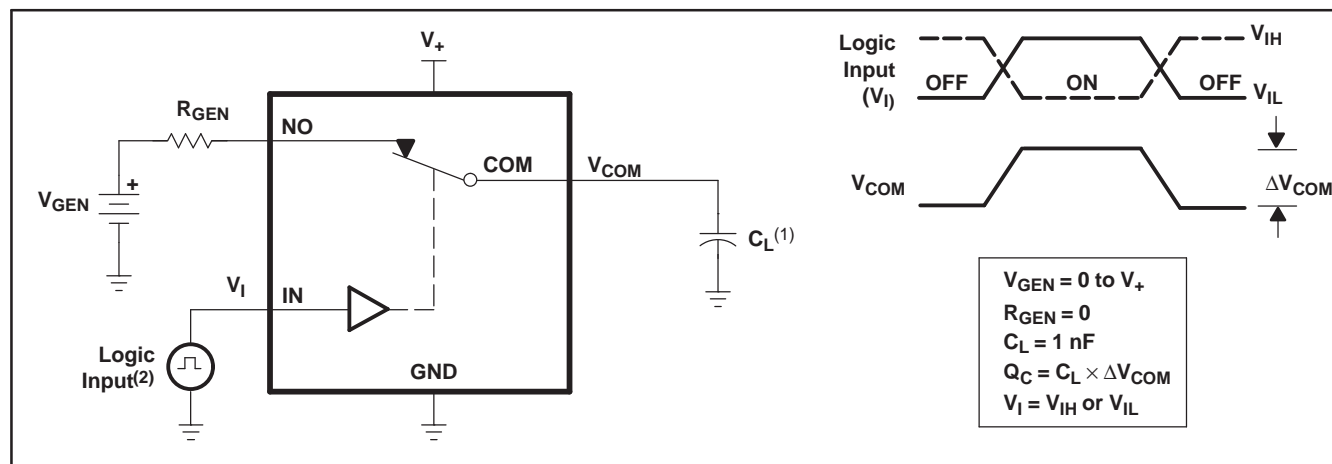


Figure 22. Crosstalk (X_{TALK})

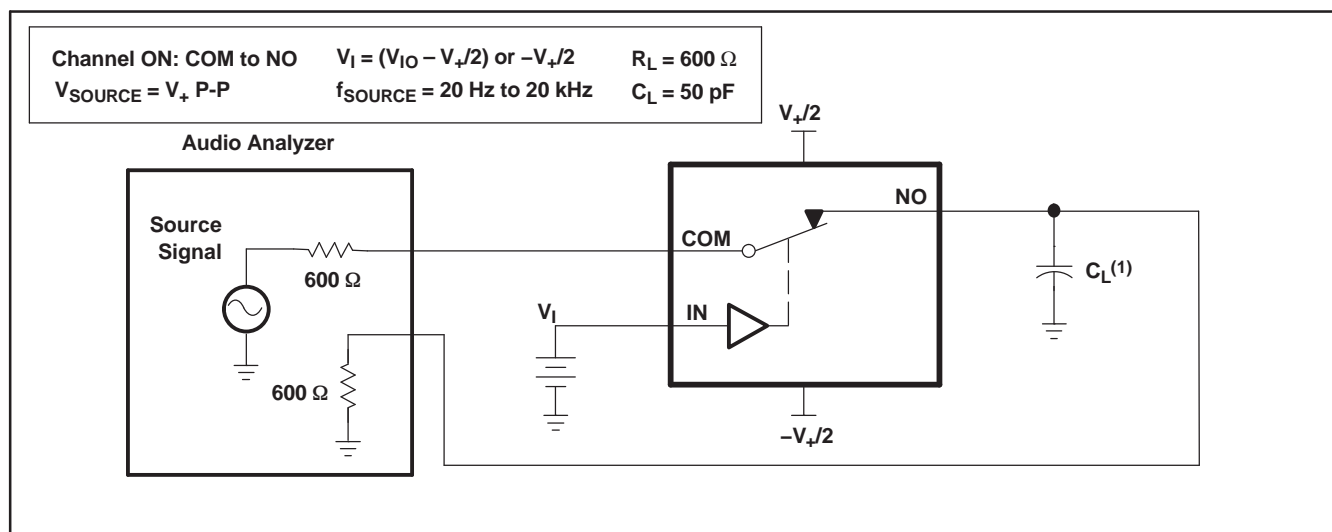
PARAMETER MEASUREMENT INFORMATION (continued)



(1) C_L includes probe and jig capacitance.

(2) All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.

Figure 23. Charge Injection (Q_C)



(1) C_L includes probe and jig capacitance.

Figure 24. Total Harmonic Distortion (THD)

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A6542YZPR	ACTIVE	DSBGA	YZP	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(JH7 ~ JHN)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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TAPE AND REEL INFORMATION



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A6542YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A6542YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0

YZP0008



PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



EXAMPLE BOARD LAYOUT

YZP0008

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE
SCALE:40X



SOLDER MASK DETAILS
NOT TO SCALE

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NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).

EXAMPLE STENCIL DESIGN

YZP0008

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

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NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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